

UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION

PATENT NO. : 7,238,595 B2
APPLICATION NO. : 10/800390
DATED : July 3, 2007
INVENTOR(S) : Paul D. Brabant et al.

Page 1 of 1

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Item (56), under Other Publications

On Page 2, Col. 1 of List of References, delete "Domonstration" and insert -- Demonstration --, therefore.

On Page 2, Col. 1 of List of References, delete "high-kgate" and insert -- high-k gate --, therefore.

On Page 2, Col. 2 of List of References, delete "'Schollhorn et al., "Coalescence of germanium islands on silicon", Thin Solid Films 336:109-111 (1998)."

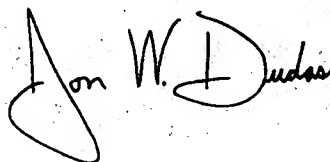
In Col. 22, line 36, delete "heteroepitaxiar" and insert -- heteroepitaxial --, therefore.

In Col. 22, line 60, delete "trisine" and insert -- trisilane --, therefore.

In Col. 23, line 17, delete "Torn" and insert -- Torr --, therefore.

Signed and Sealed this

Fourth Day of December, 2007

A handwritten signature in black ink, appearing to read "Jon W. Dudas". The signature is stylized with a large, looped initial "J" and a cursive "Dudas".

JON W. DUDAS
Director of the United States Patent and Trademark Office